

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

2SC5360

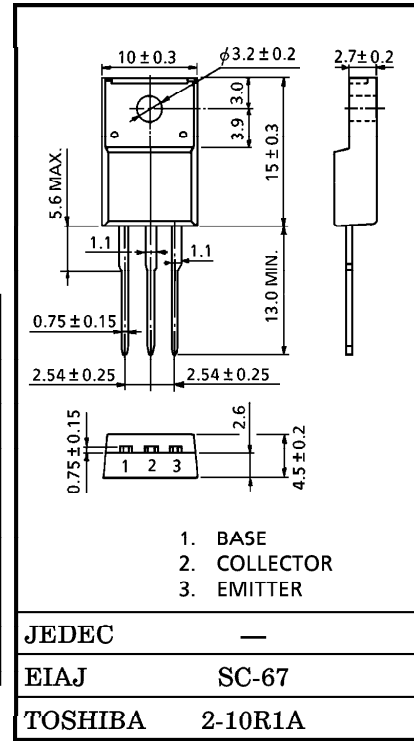
COLOR TV CHROMA OUTPUT APPLICATIONS

Unit in mm

- High Voltage : $V_{CEO} = 300V$
- Small Collector Output Capacitance : $C_{ob} = 5.0pF$ (Typ.)
- High Transition Frequency : $f_T = 100MHz$ (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	300	V
Collector-Emitter Voltage	V_{CEO}	300	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	150	mA
Base Current	I_B	50	mA
Collector Power Dissipation	P_C	Ta = 25°C 2.0	W
		Tc = 25°C 12.5	
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C



Weight : 1.7g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 240V, I_E = 0$	—	—	1.0	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 5V, I_C = 0$	—	—	1.0	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 5mA, I_B = 0$	300	—	—	V
DC Current Gain	h_{FE}	$V_{CE} = 10V, I_C = 50mA$	40	—	170	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 100mA, I_B = 20mA$	—	—	1.0	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 100mA, I_B = 20mA$	—	—	1.2	V
Transition Frequency	f_T	$V_{CE} = 10V, I_C = 30mA$	40	100	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 50V, I_E = 0, f = 1MHz$	—	5.0	6.5	pF

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